2SC3793

Silicon NPN Epitaxial

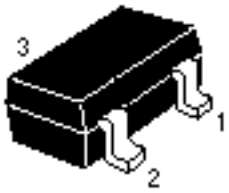
HITACHI

Application

UHF local oscillator

Outline

MPAK



1. Emitter
2. Base
3. Collector

Hitachi semiconductor

Absolute Maximum Ratings (Ta = 25°C)

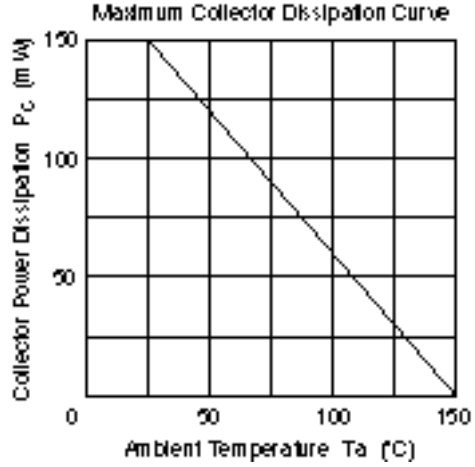
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	15	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

Electrical Characteristics (Ta = 25°C)

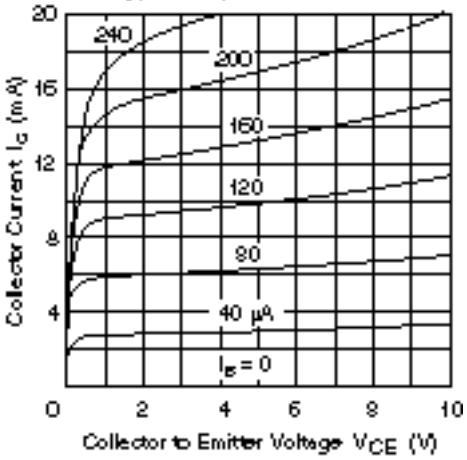
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	—	—	V	I_C = 10 µA, I_E = 0
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	15	—	—	V	I_C = 1 mA, R_{BE} = ∞
Collector cutoff current	I_{CBO}	—	—	1	µA	V_{CB} = 15 V, I_E = 0
Emitter cutoff current	I_{EBO}	—	—	1	µA	V_{EB} = 3 V, I_C = 0
DC current transfer ratio	h_{FE}	30	—	200		V_{CE} = 10 V, I_C = 5 mA
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	V	I_C = 20 mA, I_B = 4 mA
Collector output capacitance	Cob	—	0.7	1	pF	V_{CB} = 10 V, I_E = 0, f = 1MHz
Gain bandwidth product	f_T	—	2.9	—	GHz	V_{CE} = 10 V, I_C = 5 mA

Note: Marking is “IP-”.

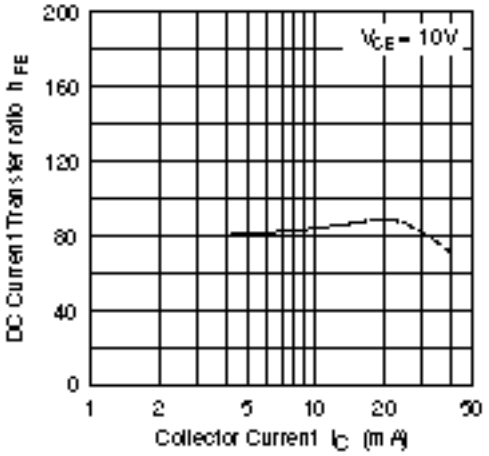
Maximum Collector Dissipation Curve



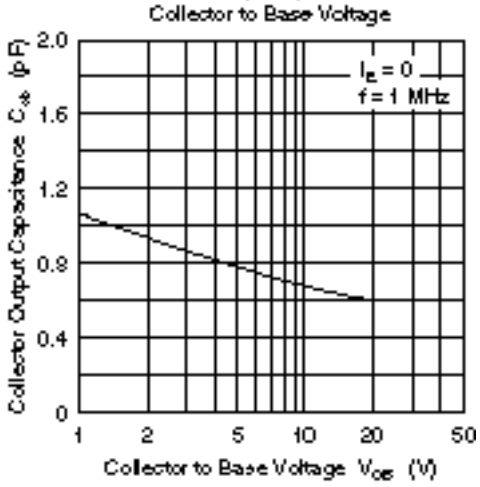
Typical Output Characteristics



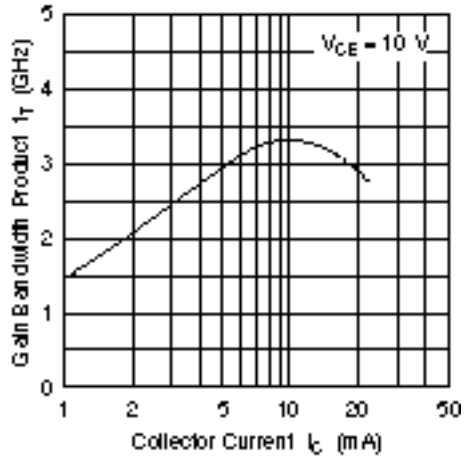
DC Current Transfer Ratio vs. Collector Current



Collector Output Capacitance vs. Collector to Base Voltage



Gain Bandwidth Product vs. Collector Current



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HITACHI

Hitachi, Ltd.
Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U.S.A.
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071